

2SC5609

Silicon PNP epitaxial planer type

For general amplification

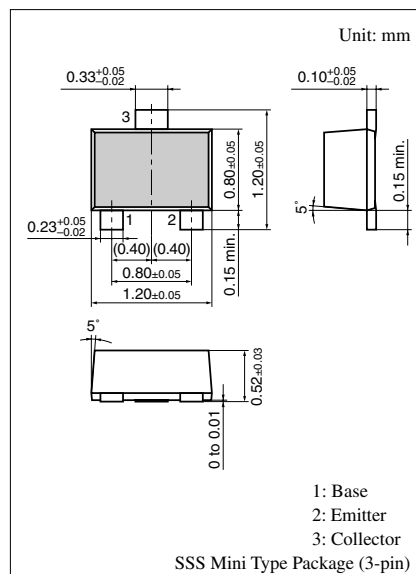
Complementary to 2SA2021

■ Features

- High forward current transfer ratio h_{FE}
- SSS-mini type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	200	mA
Collector current	I_C	100	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$



Marking Symbol: 3F

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 20\text{ V}, I_E = 0$			0.1	μA
	I_{CEO}	$V_{CE} = 10\text{ V}, I_B = 0$			100	μA
Collector to base voltage	V_{CBO}	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	60			V
Collector to emitter voltage	V_{CEO}	$I_C = 2\text{ mA}, I_B = 0$	50			V
Emitter to base voltage	V_{EBO}	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	7			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = 10\text{ V}, I_C = 2\text{ mA}$	180		390	
	h_{FE2}	$V_{CE} = 2\text{ V}, I_C = 100\text{ mA}$	90			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$		0.1	0.3	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		3.5		pF
Transition frequency	f_T	$V_{CB} = 10\text{ V}, I_E = -2\text{ mA}, f = 200\text{ MHz}$		80		MHz